

Silicon NPN Power Transistors

2SC3486

DESCRIPTION

- With TO-3PN package
- High voltage ,high speed
- Wide area of safe operation

APPLICATIONS

- For color TV display horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

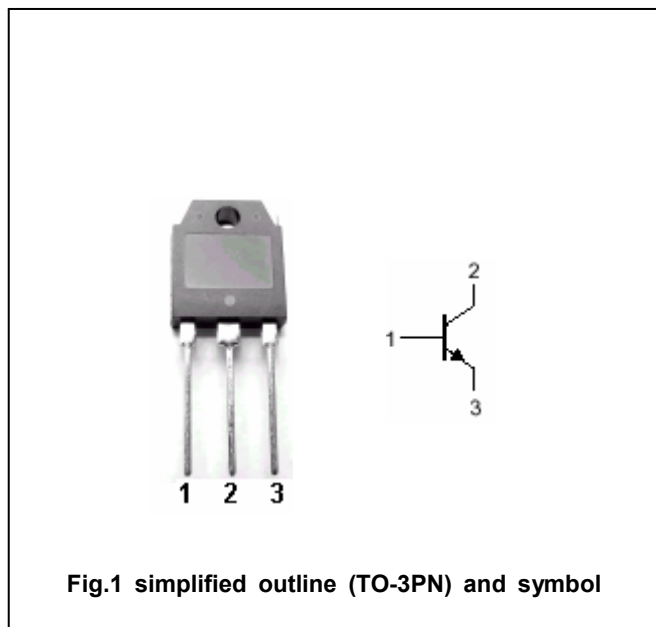


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		6	A
I_{CM}	Collector current-peak		16	A
P_C	Collector power dissipation	$T_C = 25\square$	120	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-55~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=5mA$; $R_{BE}=\infty$	800			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=5mA$; $I_E=0$	1500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=5mA$; $I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=5A$; $I_B=1.2A$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=5A$; $I_B=1.2A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800V$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V$; $I_C=0$			1	mA
h_{FE}	DC current gain	$I_C=1A$; $V_{CE}=5V$	8			
f_T	Transition frequency	$I_C=1A$; $V_{CE}=10V$		3		MHz

Switching times

t_{stg}	Storage time	$I_C=5A$; $R_L=40\Omega$ $I_{B1}=1A$; $I_{B2}=-2A$			3.0	μs
t_f	Fall time				0.3	μs

